

N-Channel Enhancement Mode Power MOSFET

Description

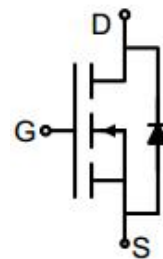
The GT025N06AM uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} 60V
- I_D (at $V_{GS} = 10V$) 170A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 2.5m Ω
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 3m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters
- Synchronous Rectification



Schematic Diagram



TO-263

Device	Package	Marking	Packaging
GT025N06AM	TO-263	GT025N06	800psc/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	170	A
Pulsed Drain Current (note1)	I_{DM}	680	A
Gate-Source Voltage	V_{GS}	± 20	V
Single pulse avalanche energy (note2)	E_{AS}	420	mJ
Power Dissipation	P_D	215	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

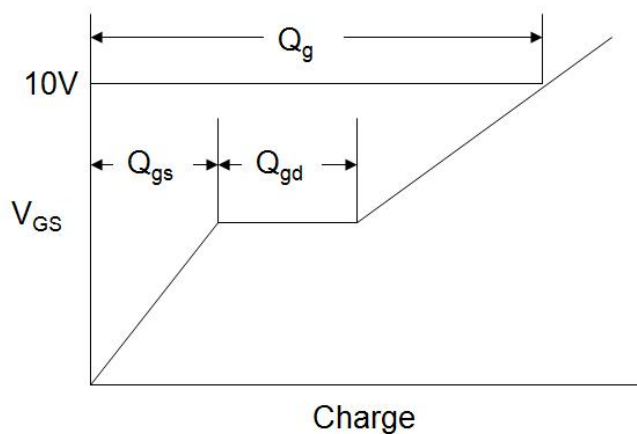
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJA}	50	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	0.58	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.6	2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 20A	--	2	2.5	mΩ
		V _{GS} = 4.5V, I _D = 15A	--	2.5	3	
Forward Transconductance	g _{FS}	V _{DS} = 5V,I _D = 20A	--	60	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 30V, f = 1.0MHz	--	5119	--	pF
Output Capacitance	C _{oss}		--	1347	--	
Reverse Transfer Capacitance	C _{rss}		--	78	--	
Total Gate Charge	Q _g	V _{DD} = 30V, I _D = 20A, V _{GS} = 10V	--	70	--	nC
Gate-Source Charge	Q _{gs}		--	21	--	
Gate-Drain Charge	Q _{gd}		--	16	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30V, I _D = 50A, R _G = 3Ω	--	16	--	ns
Turn-on Rise Time	t _r		--	9	--	
Turn-off Delay Time	t _{d(off)}		--	36	--	
Turn-off Fall Time	t _f		--	11	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	170	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 20A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Chrage	Qrr	IF=20A, di/dt=500A/us		150	--	nC
Reverse Recovery Time	Trr			30	--	ns

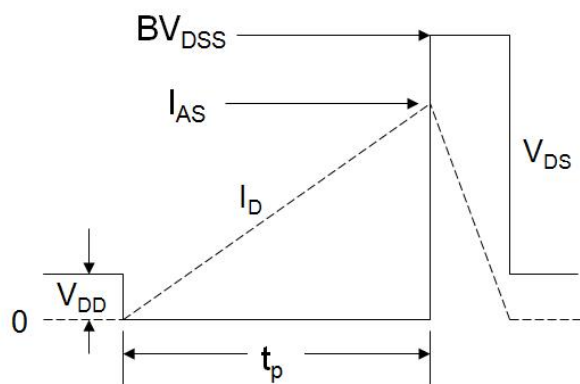
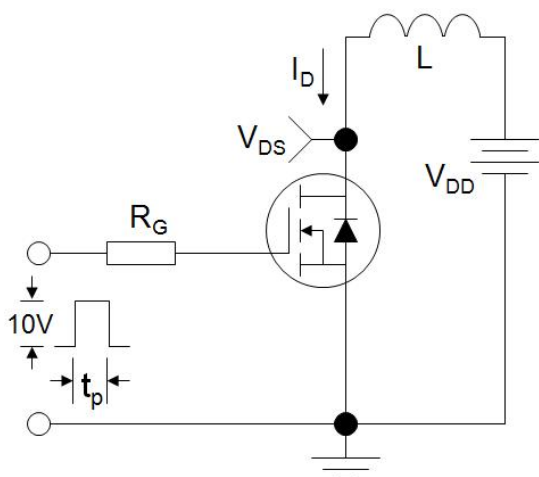
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. EAS condition : $T_J = 25^{\circ}\text{C}$, $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_g = 25\Omega$

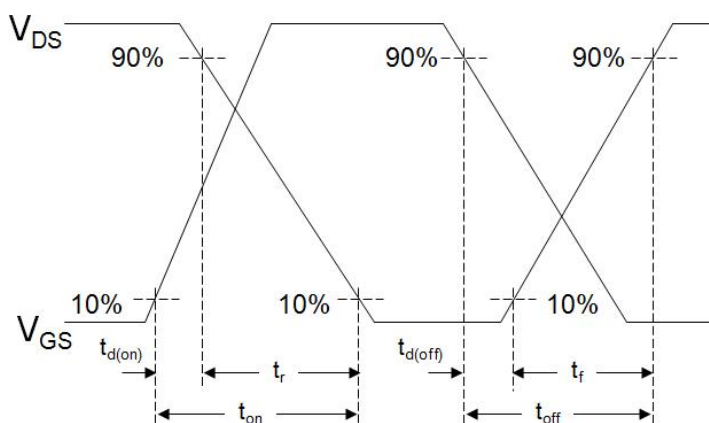
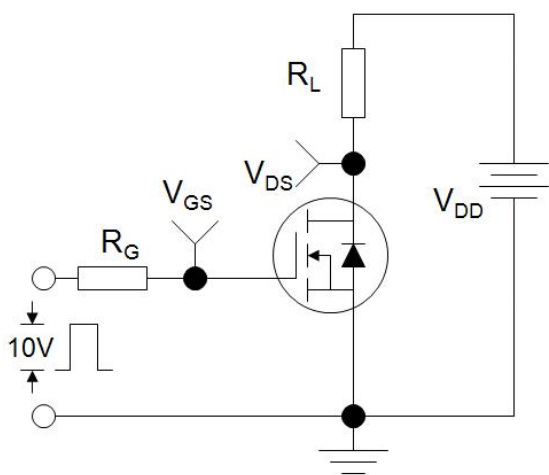
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

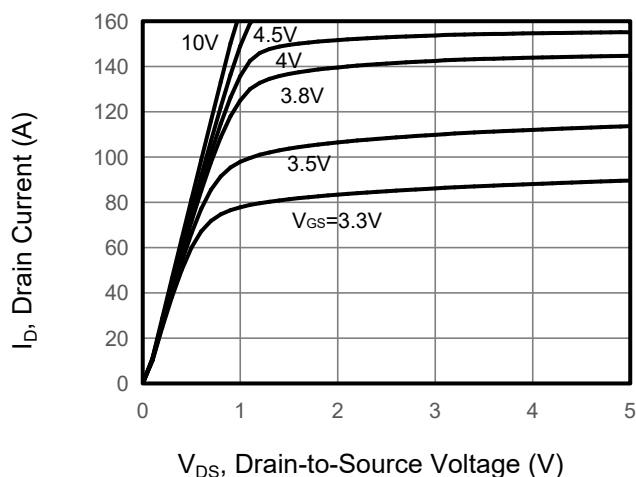


Figure 2. Transfer Characteristics

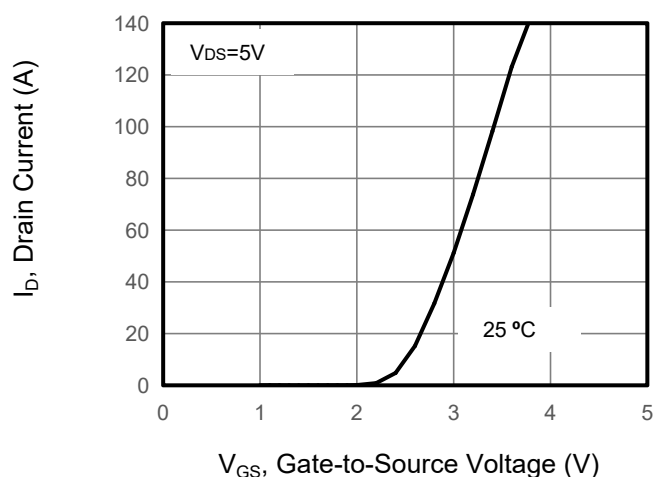


Figure 3. Drain Source On Resistance

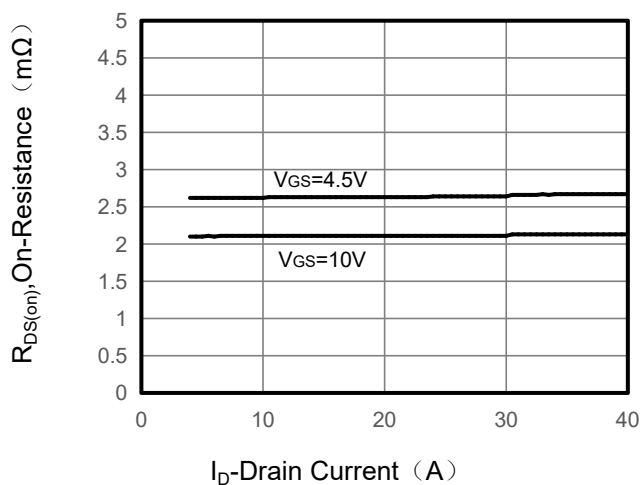


Figure 4. Gate Charge

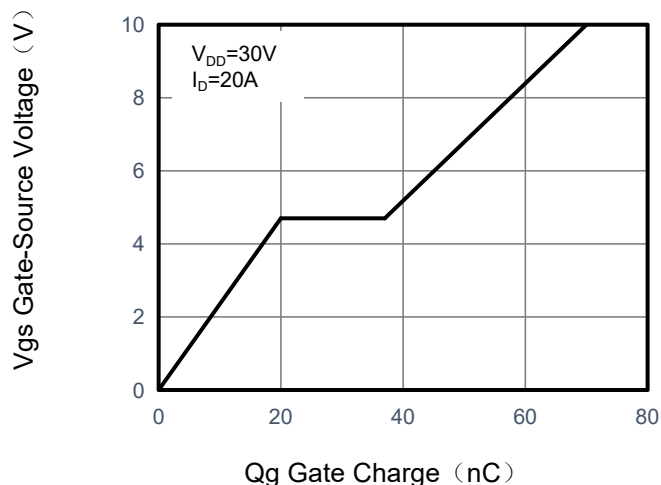


Figure 5. Capacitance vs Vds

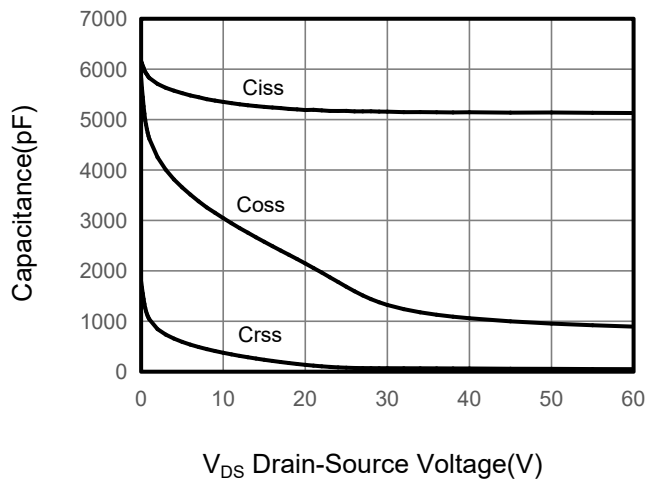
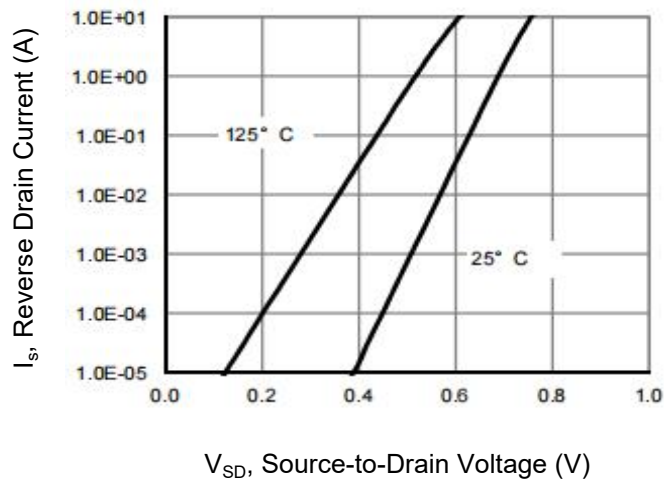


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

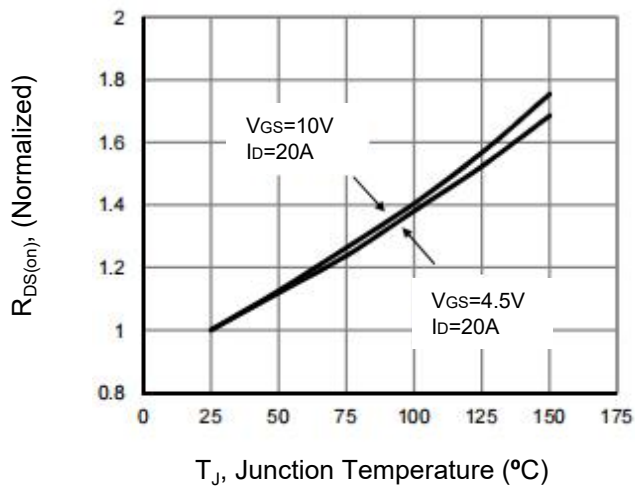


Figure 8. Safe Operation Area

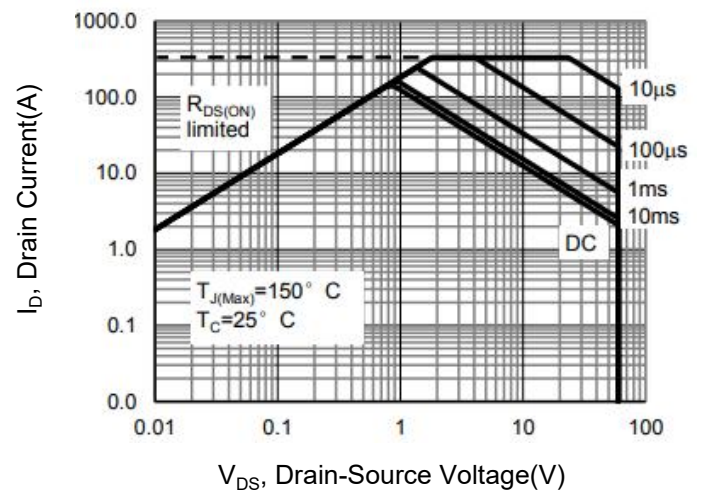
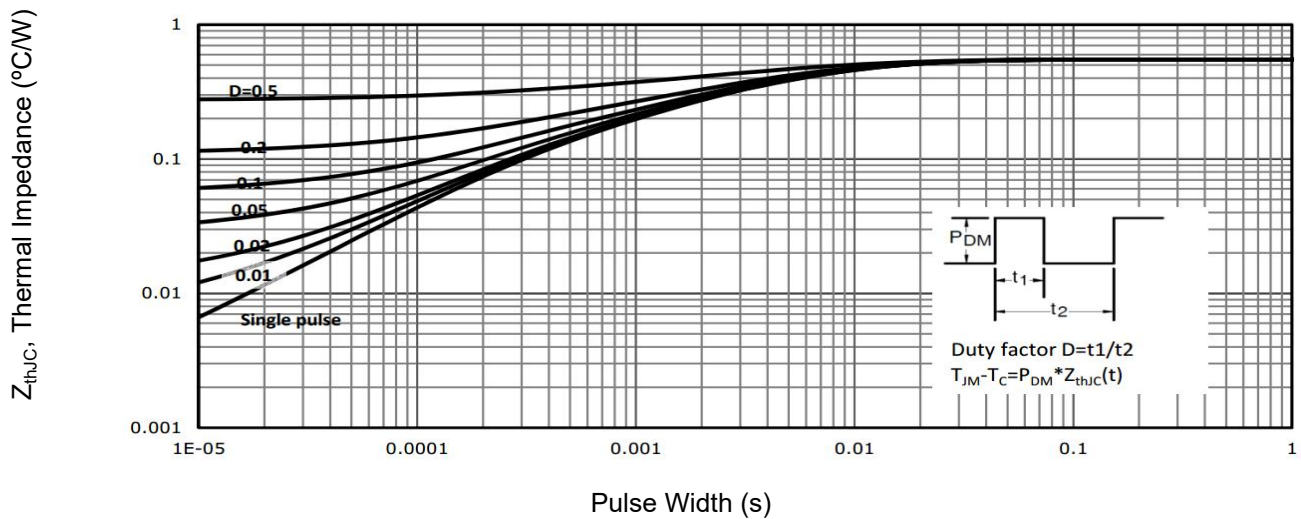
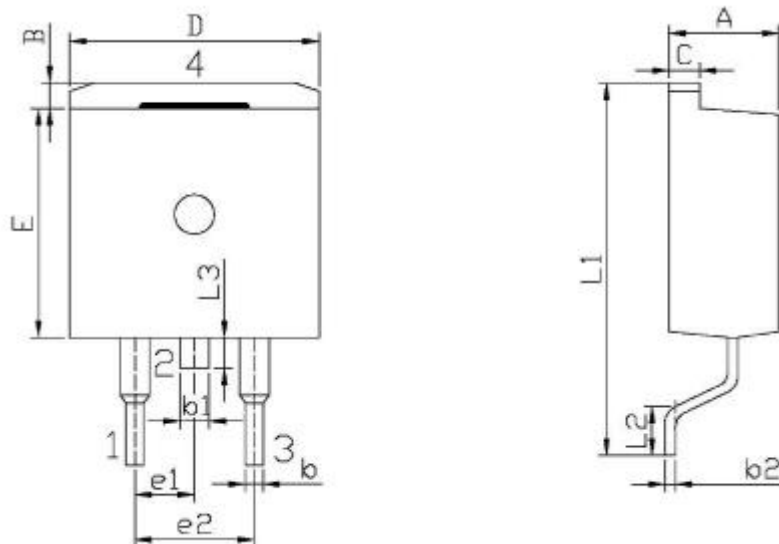


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-263 Package Mechanical Data



UNIT:mm

	MIN	MAX
A	4.30	4.70
B	1.00	1.40
b	0.70	0.90
b1	1.15	1.35
b2	0.40	0.60
C	1.20	1.40
D	9.80	10.20
E	9.00	9.40
e1	2.34	2.74
e2	4.88	5.28
L1	15.00	16.00
L2	2.24	2.84
L3	1.20	1.60